Attorney Docket No.: N1085-00154 TSMC 2003-285

Amendments to the Claims:

This Listing of Claims will replace all prior versions and listings of claims in the Application:

- 1. (Amended) A method for analyzing a semiconductor manufacturing process,5 comprising:
 - (a) generating sets of input and output data from the semiconductor manufacturing process;
 - (b) determining principal components from the set of input data by Principal Component Analysis (PCA) and <u>determining</u> a set of principal component score data [based on] <u>by multiplying the set of input data by parameters describing a relationship between</u> the principal components <u>and the input data</u>; and
 - (c) determining a relationship between the sets of input and output data from the set of principal component score data and the set of output data.
- 2. (Original) The method of claim 1, further comprising feeding back the
 relationship to the semiconductor process to predict sets of new input and output data.
 - 3. (Original) The method of claim 1, wherein the step (a) comprises generating the input and output data from a thermal diffusion process.
 - 4. (Original) The method of claim 3, further comprising performing the thermal diffusion process in a vertical furnace.
- 5. (Original) The method of claim 4, wherein the set of input data comprise different zone temperatures in the vertical furnace.
 - 6. (Original) The method of claim 4, wherein the set of output data comprise thicknesses of a thin film layer formed by the thermal diffusion process.

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7. (Original) The method of claim 1, further comprising transforming the sets of input and output data into sets of transformed input and output data by a model.

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- 8. (Original) The method of claim 7, further comprising comparing the sets of input and output data with the sets of transformed input and output data.
 - 9. (Original) The method of claim 7, wherein the model is an Arrhenius model.
- 10. (Original) The method of claim 1, wherein the step (c) comprises applying a regression model to determine the relationship.
- 11. (Original) The method of claim 10, wherein the regression model comprises a linear regression model.
- 10 12. (Original) The method of claim 1, further comprising applying design of experiment (DOE) to generate the set of input and output data.
 - 13. (Amended) A method for analyzing a thermal diffusion process in a vertical furnace, comprising:
 - (a) generating sets of input and output data from the thermal diffusion process by design of experiment (DOE) techniques;
 - (b) determining principal components from the sets of input data by Principal Component Analysis (PCA) and <u>determining</u> a set of principal component score data [based on] <u>by multiplying the set of input data by parameters describing a relationship between</u> the principal components <u>and the input data</u>; and
 - (c) determining a relationship between the sets of input and output data from the set of principal component score data and the set of output data.
 - 14. (Amended) The method of claim 13, wherein said determining a relationship further [comprising] comprises filtering noise within the sets of input and output data and

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feeding back the relationship to the semiconductor process for predicting sets of new input and output data.

- 15. (Original) The method of claim 13, wherein the set of input data comprise different zone temperatures in the vertical furnace.
- 5 16. (Original) The method of claim 13, wherein the set of output data comprise thicknesses of a thin film layer formed by the thermal diffusion process.
 - 17. (Original) The method of claim 13, further comprising transforming the sets of input and output data into sets of transformed input and output data by a model.
- 18. (Original) The method of claim 17, further comprising comparing the sets of input and output data with the sets of transformed input and output data.
 - (Original) The method of claim 17, wherein the model is an Arrhenius model.
 - 20. (Original) The method of claim 13, wherein the set of principal component score data comprise principal component scores.
- 21. (Original) The method of claim 13, wherein the step (c) comprises applying a regression model to determine the relationship.
 - 22. (Original) The method of claim 21, wherein the regression model comprises a linear regression model.
 - 23. (Amended) A method for analyzing a thermal diffusion process in a vertical furnace, comprising:
- 20 (a) generating a set of input data having different zone temperatures in the vertical furnace and a set of output data having thicknesses of a thin film layer by <u>design</u> of experiment (DOE) techniques;

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- (b) transforming the sets of input and output data into sets of transformed input and output data by an Arrhenius model;
- (c) comparing the sets of input and output data with the sets of transformed input and output data;
- (d) determining principal components from the sets of input data by Principal Component Analysis (PCA) and <u>determining</u> a set of principal component score data [based on] <u>by multiplying the set of input data by parameters describing a relationship between</u> the principal components <u>and the input data</u>;
- (e) determining a relationship between the sets of input and output data from the
 set of principal component scores and the set of output data by a linear regression model; and
 - (f) feeding back the relationship to the semiconductor process to predict sets of new input and output data.
- 24. (Amended) A system for analyzing a thermal diffusion process in a vertical furnace, [comprising,] comprising:

at least one storing means adapted to store sets of input data and output data from [the] <u>a</u> semiconductor manufacturing process; and

at least one processor coupled to the storing means, adapted to determine principal components from the sets of input data by <u>Principal</u> Component Analysis (PCA) and <u>to determine</u> a set of principal component score data [based on] <u>by multiplying the set of input data by parameters describing a relationship between</u> the principal components <u>and the input data</u>, and <u>further adapted to determine a relationship between the sets of input and output data from the set of principal component score data and the set of output data.</u>

25. (Original) The system of claim 24, wherein the processor further is adapted to feed back the relationship to the storing means, and predicts sets of new input and output data.

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26. (Original) The system of claim 24, wherein the set of input data comprise different zone temperatures in the vertical furnace.

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- 27. (Original) The system of claim 24, wherein the set of output data comprise thicknesses of a dielectric layer formed by the thermal diffusion process.
- 5 28. (Original) The system of claim 24, wherein the processor further is adapted to transform the sets of input and output data into sets of transformed input and output data by a model.
- 29. (Original) The system of claim 28, wherein the processor further is adapted to compare the sets of input and output data with the sets of transformed input and output 10 data.
 - 30. (Original) The system of claim 28, wherein the model is an Arrhenius model.
 - 31. (Original) The system of claim 24, wherein the processor is adapted to determine the relationship by using a regression model.
- 32. (Original) The system of claim 31, wherein the regression model comprises a 15 linear regression model.
 - 33. (Original) The system of claim 24, where the sets of input and output data are generated by design of experiment (DOE).
 - 34. (New) A method for analyzing a semiconductor manufacturing process, comprising:
- 20 (a) generating sets of input and output data from the semiconductor manufacturing process;

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- (b) determining principal components from the set of input data by Principal Component Analysis (PCA) and determining a set of principal component score data based on the principal components;
- (c) determining a relationship between the sets of input and output data from the set of principal component score data and the set of output data;
 - (d) filtering noise within the sets of input and output data to determine a filtered relationship; and
 - (e) feeding back the filtered relationship to the semiconductor process to predict sets of new input and output data.
- 35. (New) A system for analyzing a thermal diffusion process in a vertical furnace, comprising:

at least one storing means adapted to store sets of input data and output data from [the] a semiconductor manufacturing process; and

at least one processor coupled to the storing means, adapted to:

determine principal components from the sets of input data by Principal Component
Analysis (PCA); to determine a set of principal component score data based on the
principal components; to determine a relationship between the sets of input and output
data from the set of principal component score data and the set of output data; to filter
noise within the sets of input and output data and determine a filtered relationship; and
to feed back the filtered relationship to the semiconductor process to predict sets of new
input and output data.